

ABSTRACT OF THE DISCLOSURE

A complementary field effect transistor comprises: a semiconductor substrate; an n-type field effect transistor provided on the semiconductor substrate; and a p-type field effect transistor provided on the semiconductor substrate. The n-type field effect transistor has: a first gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and further containing a compound of the element and a group III element; a first gate electrode provided on the first gate insulating film; and n-type source and drain regions formed on both sides of the first gate electrode.

The p-type field effect transistor has: a second gate insulating film containing an oxide including an element selected from the group consisting of group IV metals and Lanthanoid metals, and including substantially no positive charge; a second gate electrode provided on the second gate insulating film; and p-type source and drain regions provided on both sides of the second gate electrode.